

# **isc Silicon PNP Power Transistor**

### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= -100V(Min)
- · High DC Current Gain
- · Low Saturation Voltage
- Complement to Type BD829
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

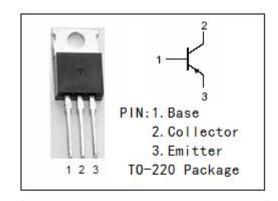
 Designed for driver-stages in hi-fi amplifiers and television circuits.

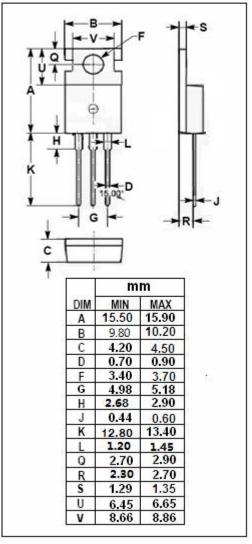
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-100	V	
$V_{\text{CEO}}$	Collector-Emitter Voltage	-100	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
Ic	Collector Current-Continuous	-1.0	Α	
I <sub>CP</sub>	Collector Current-Peak	-1.5	Α	
P <sub>C</sub>	Collector Power Dissipation @ Ta=25°C	2	W	
	Collector Power Dissipation @ T <sub>C</sub> =25°C	10		
TJ	Junction Temperature		$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-65~150	${\mathbb C}$	

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	12.5	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient		°C/W







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**BD830** 

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-100			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =- 500mA; I <sub>B</sub> = -50mA			-0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	Ic= -0.5A ; VcE= -2V			-1.0	V
І <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = -30V; I <sub>E</sub> = 0			-0.1	- uA
		V <sub>CB</sub> =-30V; I <sub>E</sub> = 0; T <sub>C</sub> = 125℃			-10	
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-10	uA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -5mA ; V <sub>CE</sub> = -2V	25			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -150mA ; V <sub>CE</sub> = -2V	40		250	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = -500mA ; V <sub>CE</sub> =- 2V	25			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -50mA ; V <sub>CE</sub> =- 5V		75		MHz

### **NOTICE:**

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